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List of Patents and Publications for Applicant

Applicant
Karsten Wieczorek, Rolf Geilenkeuser and Jörg-Oliver Weidner

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Filing Date:
August 27, 2003Group:
2811U.S. Patent Documents
See Page 1Foreign Patent Documents
See Page 1Other Art
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U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
JS	A1	6,472,233 B1	10/29/02	Ahmed <i>et al.</i>	438	14	
	A2	2002/0033710 A1	3/21/02	Kim	324	765	
	A3						
	A4						
	A5						

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
JS	B1	DE 100 10 285 A1	9/13/01	Germany	H01L	23/544	No
	B2						
	B3						

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
JS	C1	Kim <i>et al.</i> , "Breakdown Phenomena in MIS Structure," <i>Proc. Of 3rd Int'l Conf. on Properties and Application of Dielectric Materials</i> , Tokyo, Japan, pp. 164-168, July 8-12, 1991.
JS	C2	Shanware <i>et al.</i> , "Reliability evaluation of HiSiON gate dielectric film with 12.8 Å SiO ₂ equivalent thickness," <i>IEEE</i> , pp. 6.6.1-6.6.4, 2001.
JS	C3	Abadeer <i>et al.</i> , "Key measurements of ultrathin gate dielectric reliability and in-line monitoring," <i>IBM J. Res. Develop.</i> , 43:407-16, 1999.

EXAMINER:

DATE CONSIDERED:

1-4-05

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